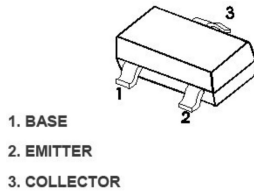


SOT-23
SOT-23 贴片塑封三极管
SOT-23 Plastic-Encapsulate Transistors

特征 Features

- Complementary to APT856/857/858
- Power Dissipation of 200mW
- Ideally suited for automatic insertion
- For switching and AF amplifier applications

机械数据 Mechanical Data

- Small Outline Plastic Package
- Epoxy UL: 94V-0
- Mounting Position: Any

Marking:

ANT846AAX0=1A	ANT846BAX0=1B	
ANT847AAX0=1E	ANT847BAX0=1F	ANT847CAX0=1G
ANT848AAX0=1J	ANT848BAX0=1K	ANT848BAX0=1L

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CB0}	846 847 848	80 50 30 V
Collector-Emitter Voltage	V _{CEO}	846 847 848	65 45 30 V
Emitter -Base Voltage	V _{EBO}		6 V
Collector Current-Continuous	I _c		100 mA
Collector Power Dissipation	P _c		200 mW
Junction Temperature	T _j		150 °C
Storage Temperature	T _{stg}		-55-+150 °C
Thermal resistance From junction to ambient	R _{θJA}		625 °C/W

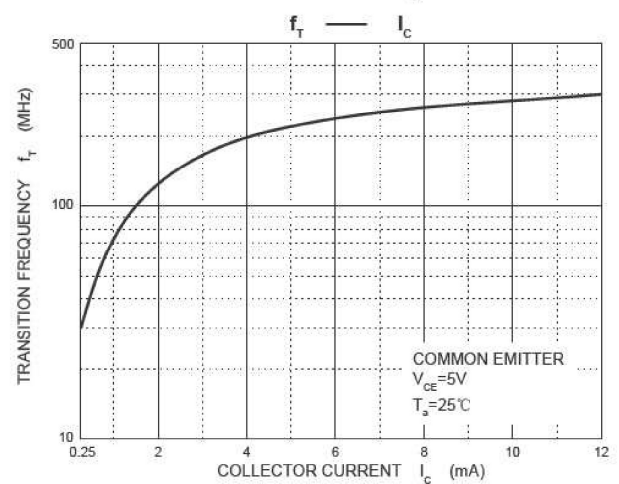
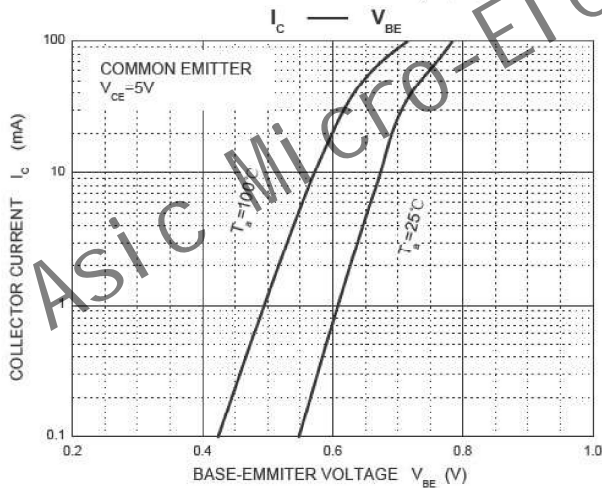
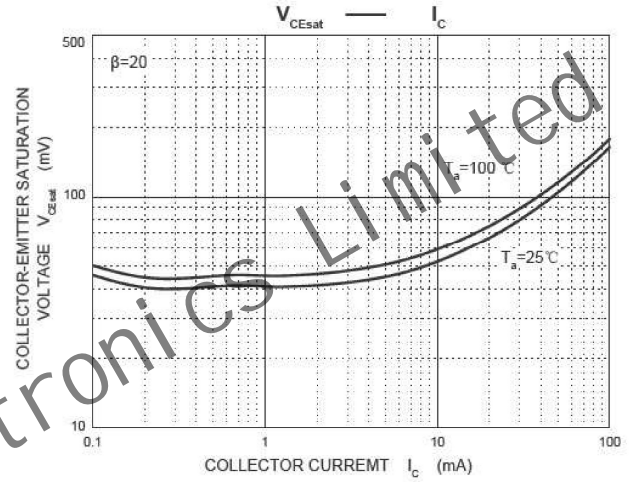
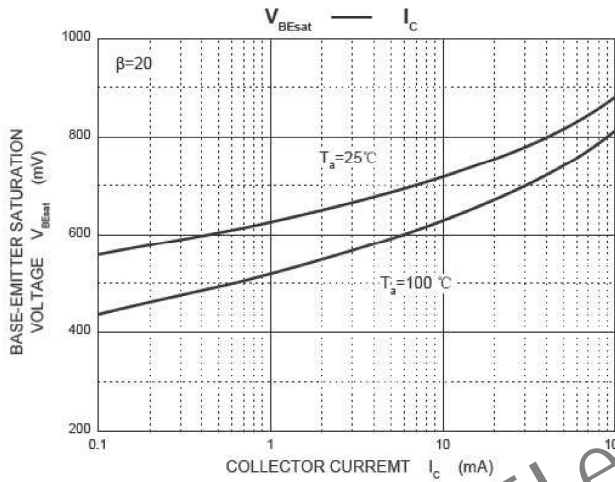
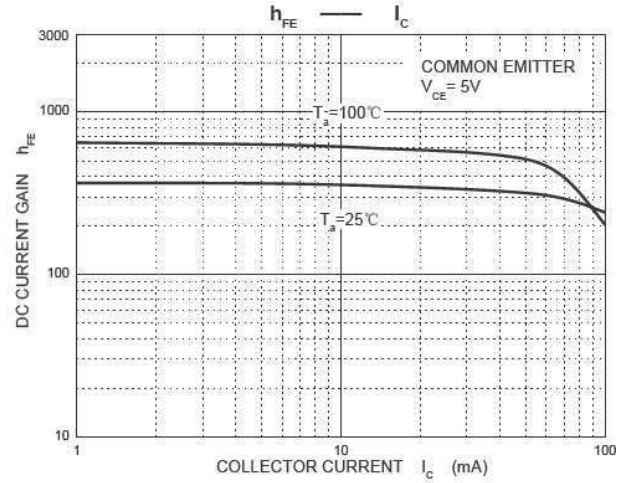
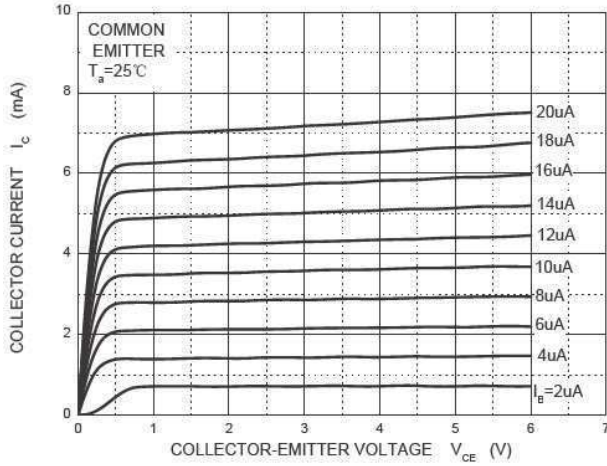
电特性 (TA = 25°C 除非另有规定)

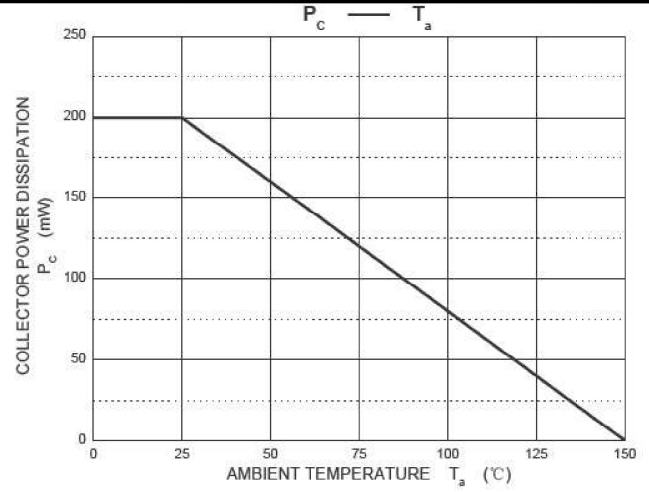
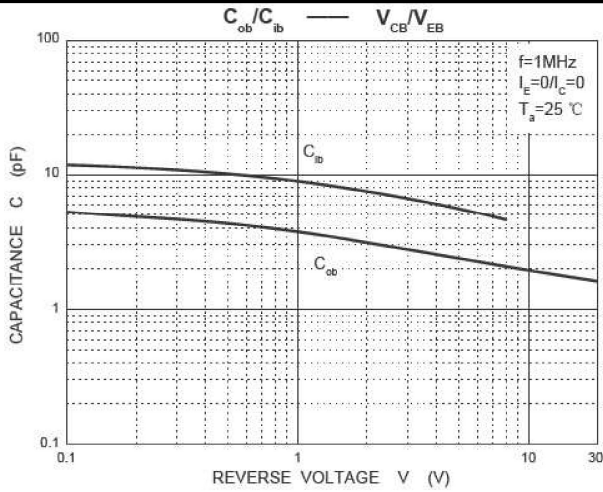
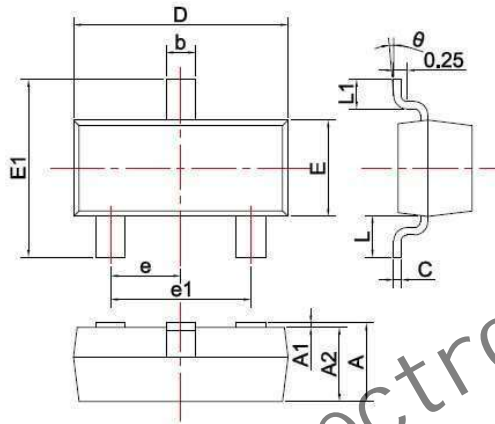
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10uA, I _E =0	846 847 848	80 50 30	V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	846 847 848	65 45 30	V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10uA, I _C =0		6	V
Collector cut-off current	I _{CBO}	V _{CB} =70V, I _E =0 V _{CB} =50V, I _E =0 V _{CB} =30V, I _E =0	846 847 848	100	nA
Collector cut-off current	I _{CEO}	V _{CE} =60V, I _B =0 V _{CE} =45V, I _B =0 V _{CE} =30V, I _B =0	846 847 848	100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		100	nA
DC current gain	h _{FE}	V _{CE} =5V, I _C =2mA	846A,847A,848A 846B,847B,848B 847C,848C	110 200 420	220 450 800
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =5mA		0.50	V
Base -emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =5mA		1.10	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=100MHz		100	MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, f=1MHz		4.5	pF

Typical characteristics

Static Characteristic



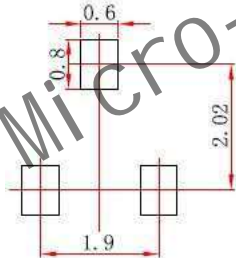

SOT-23 PACKAGE OUTLINE Plastic surface mounted package


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	8°	

Unit: mm

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
1. Controlling dimension; in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.